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Part Number Customer						
Category	Parameter		Specification	Measurement Method		
OverallWafer	1.0	Diameter	150.00 +/- 0.50 mm			
	2.0	Primary Flat Orientation	{110}+/-1.0 degree	Wafer Vendor		
	3.0	Primary Flat Length	57.50 +/- 2.50 mm	Wafer Vendor		
	4.0	Secondary Flat Orientation	None	Wafer Vendor		
	5.0	Overall Thickness	450.00 +/- 12.00 μm	ADE, 100%		
	6.0	Total Thickness Variation (TTV)	<5.00µm	Guaranteed by Process		
	7.0	Bow	<60.00µm	ADE to ASTM F534, 20%		
	8.0	Warp	<60.00µm	ADE to ASTM F657, 20%		
	9.0	Edge Chips	0	Bright Light, 100% (note 2)		
	10.0	Edge Exclusion	5mm			
HandleSilicon	11.0	Handle Growth Method	CZ	Wafer Vendor		
	12.0	Handle Orientation	{100} +/- 1 degree	Wafer Vendor		
	13.0	Handle Thickness	300.00 +/- 10.00 μm	ADE, 100%		
	14.0	Handle Doping Type	Р	Wafer Vendor		
	15.0	Handle Dopant	Boron	Wafer Vendor		
	16.0	Handle Resistivity	0.005 - 0.01 Ohmcm	Wafer Vendor		
	17.0	Backside Finish	Polished with laser marking	Guaranteed by process		
BuriedOxide	18.0	Oxide Type	NONE	Guaranteed by process		
DeviceSilicon	19.0	Device Growth Method	FZ	Wafer Vendor		
	20.0	Device Orientation	{100} +/- 1 degree	Wafer Vendor		
	21.0	Nominal Thickness	150.00 +/- 2.00 μm	ADE Single point, 100%.		
	22.0	Distance to device silicon edge from wafer edge	<= 2.0mm	Typical by process		
	23.0	Device Doping Type	Р	Wafer Vendor		
	24.0	Device Dopant	Boron	Wafer Vendor		
	25.0	Device Resistivity	>5000 Ohmcm	Wafer Vendor		
	26.0	Voids	0	Bright Light, 100% (note 2)		
	27.0	Scratches	0	Bright Light, 100% (note 2)		
	28.0	Haze	none	Bright Light, 100% (note 2)		

Icemos Technology Ltd

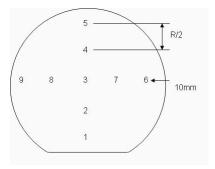
Product Specification

1000.521002

Part Number		Customer		
Category	Parameter	Specification	Measurement Method	
Shipping Details	Wafer per box :	Max 25		
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 150.00mm Antistatic Double Bagging		
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness		
Explanatory Notes	1. Microscope inspect	tion performed using microscope scan as below. 5x objective.		

2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information